

**Silicon PNP Power Transistor**

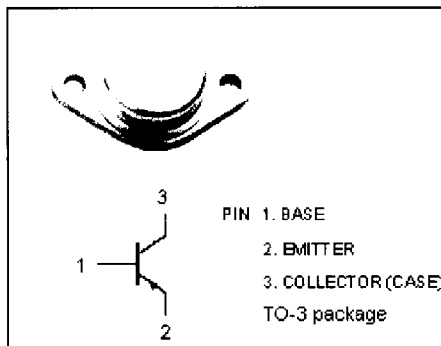
**2SA882**

**DESCRIPTION**

- High Power Dissipation-  
 :  $P_C = 100W(\text{Max.})@T_C=25^\circ C$
- Collector-Emitter Breakdown Voltage-  
 :  $V_{(BR)CEO} = -130V(\text{Min.})$

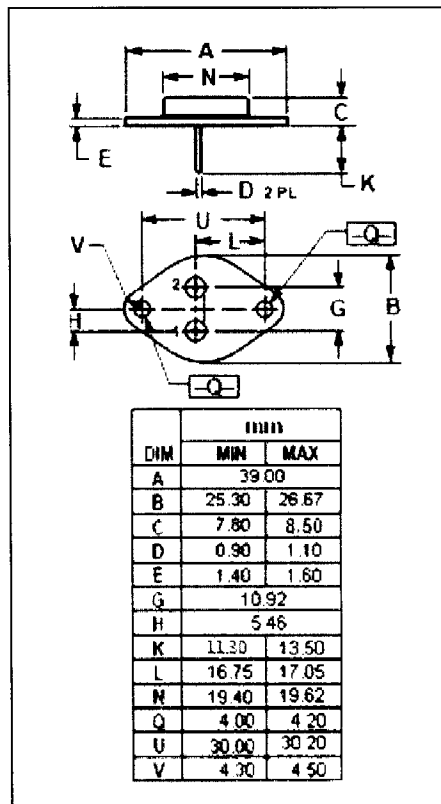
**APPLICATIONS**

- Designed for power and switching applications.

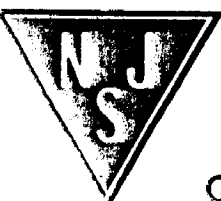


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-130	V
$V_{CEO}$	Collector-Emitter Voltage	-130	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-7	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ C$	100	W
$T_j$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-65~200	$^\circ C$



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## ELECTRICAL CHARACTERISTICS

$T_j=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}; I_B = 0$	-130			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -0.3\text{A}$			-1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -7\text{A}; I_B = -1.5\text{A}$			-3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -3\text{A}; V_{CE} = -4\text{V}$			-1.6	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -130\text{V}; I_E = 0$			-0.1	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-0.1	mA
$h_{FE-1}$	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -4\text{V}$	40			
$h_{FE-2}$	DC Current Gain	$I_C = -3\text{A}; V_{CE} = -4\text{V}$	20			